

MADP-011028-14150T

High Power PIN Diode
50 MHz - 12 GHz

Rev. V3

Electrical Specifications: $T_A = +25^\circ\text{C}$

Parameter	Test Conditions	Units	Min.	Typ.	Max.
Forward Voltage	+50 mA D.C.	V	0.7	0.9	1.1
Reverse Leakage Current	-200 V D.C.	nA	—	- 20	-1000
Total Capacitance ⁵	-50 V @ 1 MHz	pF	—	0.24	0.30
Series Resistance ⁶	+10 mA @ 1 GHz	Ω	—	3.4	4.4
Parallel Resistance ⁶	-Vdc = -40 V, @ 100 MHz	K Ω	—	500	—
Minority Carrier Lifetime	+If = 10 mA / -Ir = -6 mA (50% Control Voltage, 90% Output Voltage)	μs	—	2.0	3.0
C.W. Thermal Resistance (Infinite Heat Sink at Thermal Ground Plane)	I High = 4 A, I low = 10 mA @ 10 kHz	$^\circ\text{C}/\text{W}$	—	35	—
Power Dissipation ^{7,8} (Infinite Heat Sink at Thermal Ground Plane)	+If = 50 mA @ 1 GHz	W	—	4.3	—
Insertion Loss	F = 1 GHz, -Vdc = -10 V	dB		0.05	
Isolation	F = 1 GHz, +I bias = +10 mA	dB	16.5	18.5	

5. C_t (Total Capacitance) = C_J (Junction Capacitance) + C_p (Parasitic Package Capacitance).

6. R_s and R_p are measured on an HP4291A Impedance Analyzer.

7. De-rate power dissipation linearly by $-28.6 \text{ mW}/^\circ\text{C}$ to 0 W @ $+175^\circ\text{C}$: $P_d(T) = P_d(+25^\circ\text{C}) - \Delta P = P_d(+25^\circ\text{C}) - (28.6 \text{ mW}/^\circ\text{C})(\Delta T)$.

8. $PD = \Delta T_j / \Theta$ or $PD = (I_F + I_{RF})^2 (R_s)$, where I_F is the forward bias DC current and I_{RF} is the forward bias RMS RF current.

Absolute Maximum Ratings^{9,10}

Parameter	Absolute Maximum
D.C. Forward Voltage @ +250 mA	1.2 V
D.C. Forward Current	250 mA
D.C. Reverse Voltage	-200V
Junction Temperature	+175 $^\circ\text{C}$
Operating Temperature	-65 $^\circ\text{C}$ to +125 $^\circ\text{C}$
Storage Temperature	-65 $^\circ\text{C}$ to +150 $^\circ\text{C}$
Re-flow Temperature	+260 $^\circ\text{C}$ for 360 seconds

9. Exceeding any one or combination of these limits may cause permanent damage to this device.

10. M/A-COM Technology Solutions does not recommend sustained operation near these survivability limits.

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

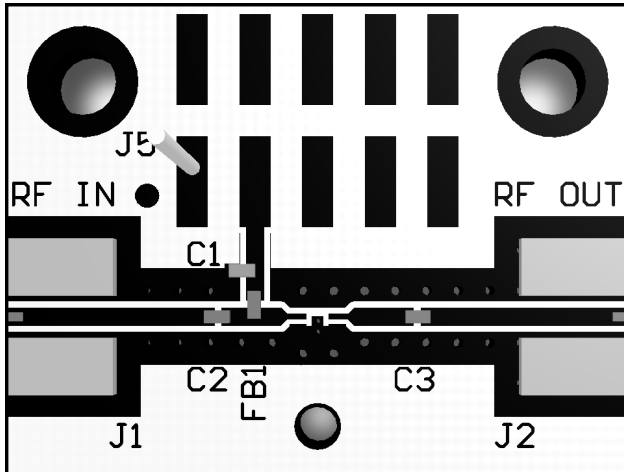
These devices are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these Class 1B devices.

MADP-011028-14150T

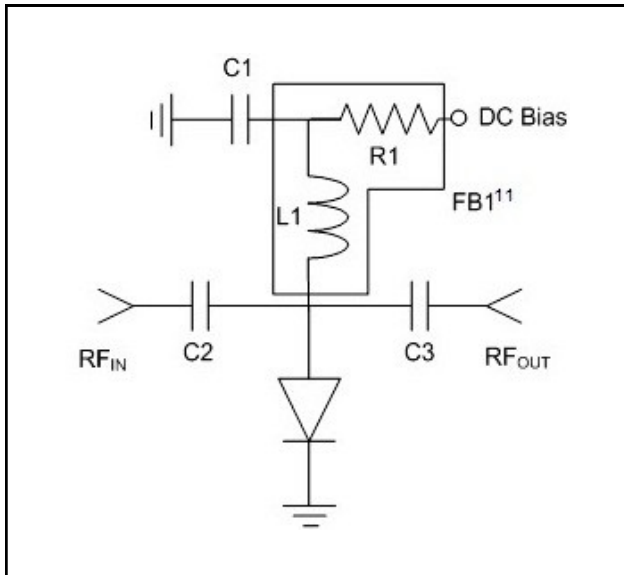
High Power PIN Diode
50 MHz - 12 GHz

Rev. V3

PCB Layout



PCB Schematic



11. R1 is not needed when using the recommended ferrite FB1.

500 - 5000 MHz Parts List¹²

Part	Value	Case Style
C1	62 pF	0402
C2, C3	100 pF	0402
FB1	470 Ω @ 1 GHz	0402
R1	150 Ω	0402
L1	82 nH	0402

12. Max DC voltage with recommended components not to exceed 100 V.

Assembly Recommendations

Devices may be soldered using standard Pb60/Sn40, or RoHS compliant solders. Leads are plated NiPdAuAg to ensure an optimum solderable connection.

For recommended Sn/Pb and RoHS soldering profile See Application Note [M538](#) on the MACOM website.

Cleanliness and Storage

These devices should be handled and stored in a clean environment. Ends of the device are NiPdAuAg plated for greater solderability. Exposure to high humidity (>80%) for extended periods may cause the surface to oxidize. Caution should be taken when storing devices for long periods.

General Handling

Device can be handled with tweezers or vacuum pickups and are suitable for use with automatic pick-and-place equipment.

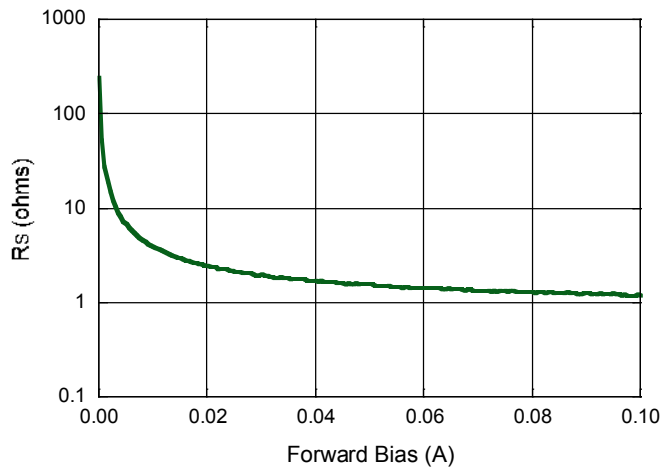
MADP-011028-14150T

High Power PIN Diode
50 MHz - 12 GHz

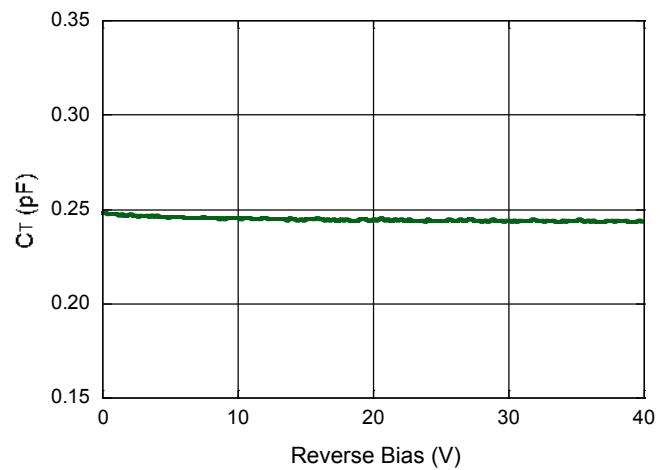
Rev. V3

Typical 1 GHz Parametric Curves

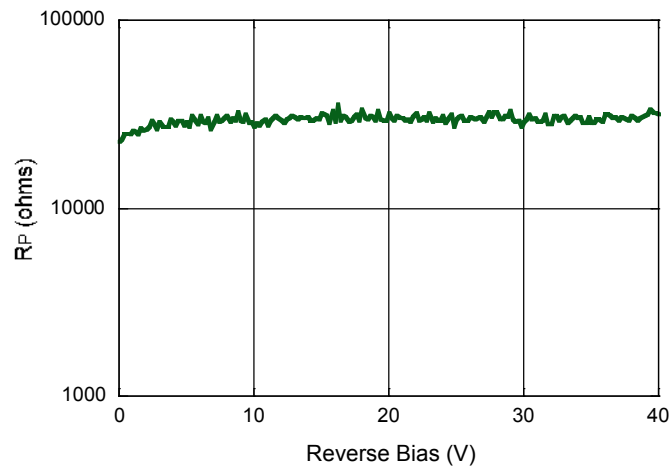
Series Resistance vs. Forward Current



Capacitance vs. Reverse Voltage



Parallel Resistance vs. Reverse Voltage



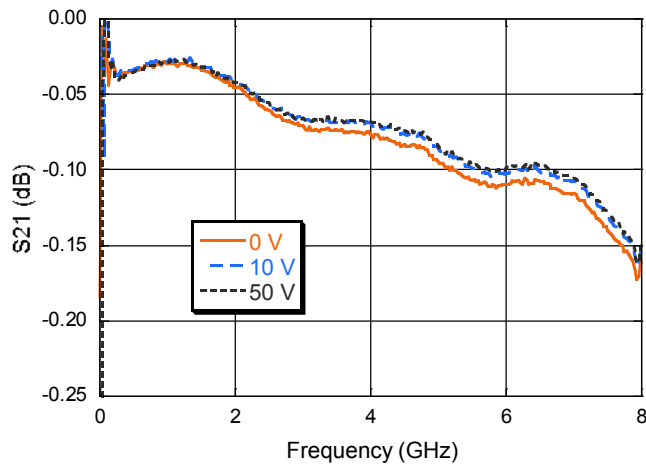
MADP-011028-14150T

High Power PIN Diode
50 MHz - 12 GHz

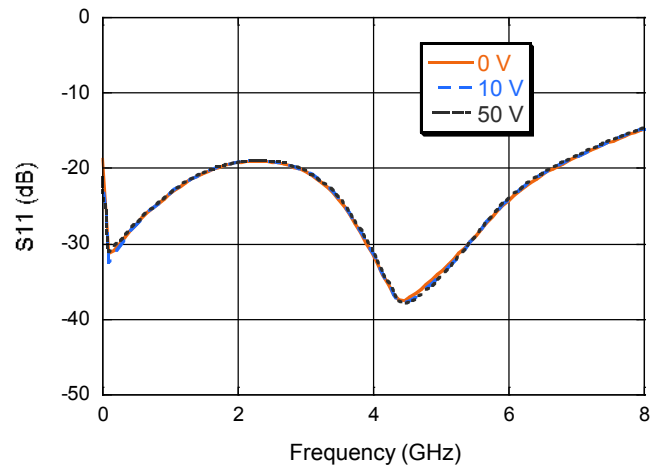
Rev. V3

Typical RF Small Signal Performance Curves

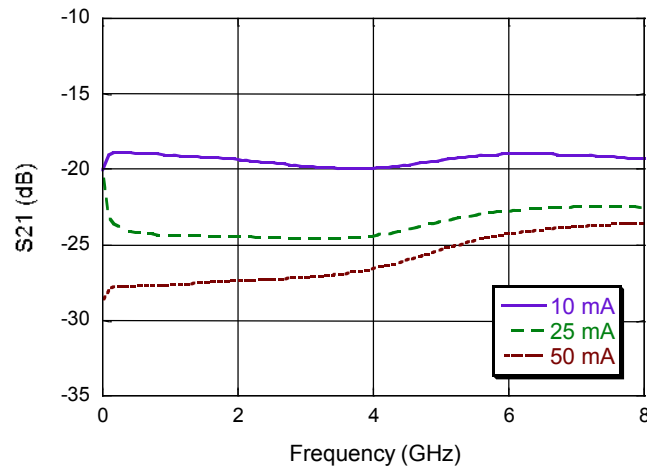
Insertion Loss



Return Loss



Isolation

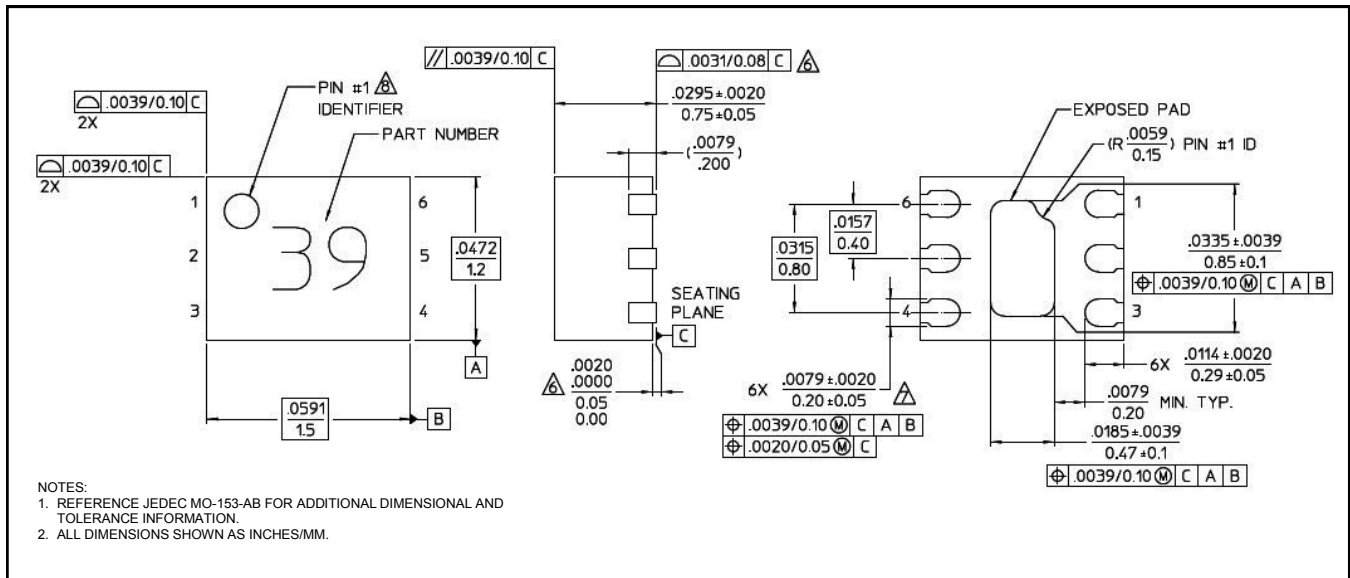


MADP-011028-14150T

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50 MHz - 12 GHz

Rev. V3

Lead-Free 1.5 x 1.2 mm 6-Lead TDFN[†]



[†] Reference Application Note [S2083](#) for lead-free solder reflow recommendations.
Meets JEDEC moisture sensitivity level 1 requirements.
Plating is NiPdAuAg.

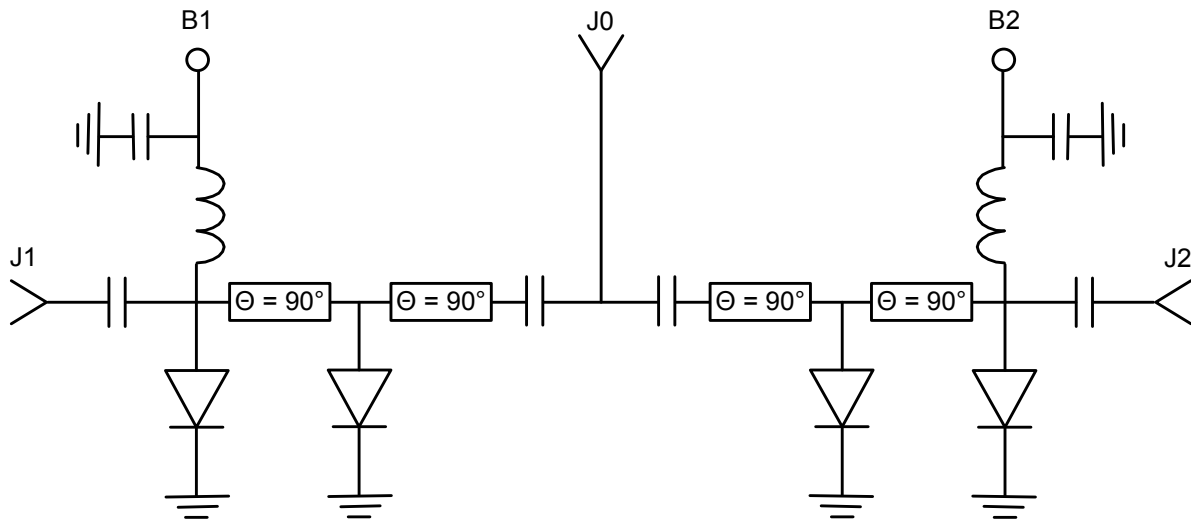
MADP-011028-14150T

High Power PIN Diode
50 MHz - 12 GHz

Rev. V3

Applications Section

Schematic of High Power SP2T Shunt Switch using MADP-011028-14150T PIN Diodes
F = Octave Bandwidth from 1 to 12 GHz
 $P_{inc} = +40$ dBm CW
 $P_{inc} = +50$ dBm, $10 \mu s$ PW, 1 % Duty



$$L = 11.807 / (\epsilon_{eff}^{1/2} * F * 4) \text{ inches, } \theta = \beta * L = (2 \pi / \lambda) * L = 90^\circ$$

Frequency is in GHz, ϵ_{eff} is Effective Dielectric Constant of Transmission Line Medium

RF State	B1 Bias	B2 Bias
J0-J1 Low Loss & J0-J2 Isolation	-50 V @ 0 mA	+1 V @ +20 mA
J0-J2 Low Loss & J0-J1 Isolation	+1 V @ +20 mA	-50 V @ 0 mA

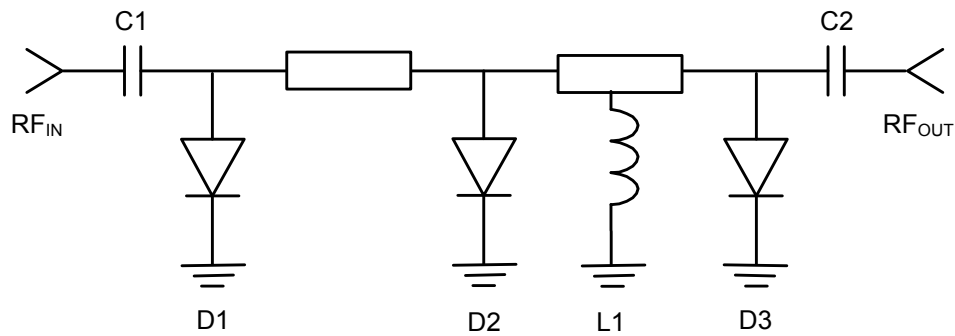
MADP-011028-14150T

High Power PIN Diode
50 MHz - 12 GHz

Rev. V3

Applications Section

Schematic of 3 Stage Limiter using MADP-011028-14150T
 $F = 1000 - 8,000 \text{ MHz}$
 $P_{inc} = +47 \text{ dBm CW}$
 $P_{inc} = +50 \text{ dBm, } 10 \mu\text{s P.W., } 1 \% \text{ Duty}$



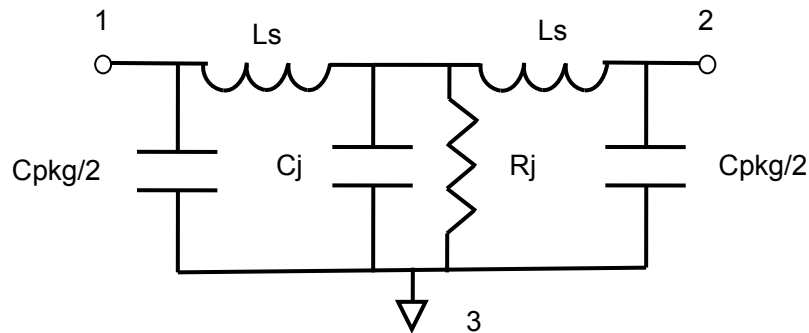
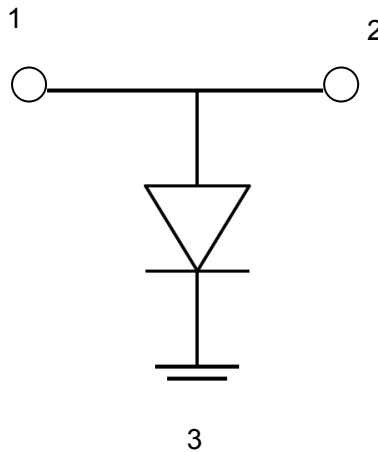
Part	PN	Case Style	Description	Quantity
D1	MADP-011028-14150T	ODS-1415	Input PIN Diode	1
D2	MADL-011023-14150T	ODS-1415	2nd Stage PIN Diode	1
D3	MADL-011023-14150T	ODS-1415	3rd Stage PIN Diode	1
L1	33 nH	0402	RF Choke / DC Return	1
C1	27 pF	0402	DC Block	1
C2	27 pF	0402	DC Block	1

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Microwave Model of MADP-011028-14150T



$R_j = R_s$ (Forward Bias Current)
 $R_j = R_p$ (Reverse Bias Voltage)

Parameter	Value
$C_{package}$	8.0E-14 F
L bond = L_s	4.0E-10 H
R_s	0.9 Ω
R_p	5E+5 Ω

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